

**IN THE SPECIFICATION:**

Please replace the paragraph at page 19, lines 4-14 with the following amended paragraph:

The transparent electrically conductive film is formed of indium oxide ( $\text{In}_2\text{O}_3$ ), an alloy of indium oxide and tin oxide ( $\text{In}_2\text{O}_3\text{-SnO}_2$ , ITO for short) or the like through the sputtering method, the vapor evaporation method or the like. The etching process of those materials is conducted by using the solution of hydrochloric acid. However, since the residue is liable to occur particularly in the etching of ITO, an alloy of indium oxide and [[tin]] zinc oxide ( $\text{In}_2\text{O}_3\text{-ZnO}$ ) may be used in order to improve the etching property. Since the alloy of indium oxide and [[tin]] zinc oxide ( $\text{In}_2\text{O}_3\text{-ZnO}$ ) is excellent in surface smoothness and also excellent in heat stability as compared with ITO, even if the terminal 104 is formed of an Al film, corrosion can be prevented. Similarly, zinc oxide (ZnO) is also a proper material, and further zinc oxide ( $\text{ZnO:Ga}$ ) to which gallium (Ga) is added may be employed in order to enhance the transmittance of the visible light and the electric conductivity.